AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A transistor structure formed in a semiconductor material of a first conductivity type, the semiconductor material having a top surface, the transistor structure comprising:

a plurality of spaced-apart second conductivity strips formed in the semiconductor material, the plurality of second conductivity strips including alternating drain and source strips;

a plurality of spaced-apart gate strips formed over the semiconductor material between the second conductivity strips;

~~an interconnect structure formed over the plurality of second conductivity strips and the plurality of gate strips, the interconnect structure being electrically connected to the second conductivity strips;~~ and

a metal structure formed directly over the ~~interconnect structure~~ plurality of second conductivity strips, the metal structure including a plurality of spaced-apart first metal strips that are electrically connected to the drain strips, the plurality of first metal strips having widths, lengths, and thicknesses such that each first metal strip has a width, a length that is substantially longer than the width, and a thickness measured normal to the top surface of the semiconductor material, the widths of the first metal strips being different.

2. (Currently Amended) ~~The transistor structure of claim 1 wherein~~ A transistor structure formed in a semiconductor material of a first conductivity type, the transistor structure comprising:

a plurality of second conductivity strips formed in the semiconductor material, the plurality of second conductivity strips including alternating drain and source strips;

a plurality of gate strips formed over the semiconductor material between the second conductivity strips;

an interconnect structure formed over the plurality of second conductivity strips and the plurality of gate strips, the interconnect structure being electrically connected to the second conductivity strips; and

a metal structure formed over the interconnect structure, the metal structure including a plurality of first metal strips that are electrically connected to the drain strips, the plurality of first metal strips having widths, lengths, and thicknesses such that each first metal strip has a width, a length, and a thickness, the widths of the first metal strips ~~are~~ being different.

3. (Original) The transistor structure of claim 2 wherein:

the plurality of first metal strips include a first center metal strip and a first outer metal strip, and

the widths of the first metal strips increase from the first center metal strip to the first outer metal strip.

4. (Currently Amended) The transistor structure of claim 2 wherein the metal structure further includes a first metal connector, the plurality of first metal strips contacting ~~that~~ the first metal connector and extending away from the first metal connector.

5. (Original) The transistor structure of claim 2 wherein each first metal strip is electrically connected to each drain strip.

6. (Original) The transistor structure of claim 2 wherein the metal structure further includes a plurality of second metal strips formed between the plurality of first metal strips, the plurality of second metal strips being electrically

connected to the source strips, the plurality of second metal strips having widths, lengths, and thicknesses such that each second metal strip has a width, a length, and a thickness.

7. (Currently Amended) The transistor structure of claim 6 wherein the widths of the ~~source~~ second metal strips are different.

8. (Original) The transistor structure of claim 7 wherein:

the plurality of second metal strips include a second center metal strip and a second outer metal strip, and

the widths of the second metal strips increase from the second center metal strip to the second outer metal strip.

9. (Currently Amended) The transistor structure of claim 7 wherein the metal structure further includes a second metal connector, the plurality of second metal strips contacting ~~that~~ the second metal connector and extending away from the second metal connector.

10. (Original) The transistor structure of claim 7 wherein each second metal strip is electrically connected to each source strip.

11. (Original) The transistor structure of claim 3 wherein the metal structure further includes a plurality of second metal strips formed between the plurality of first metal strips, the plurality of second metal strips being electrically connected to the source strips, the plurality of second metal strips having widths, lengths, and thicknesses such that each second metal strip has a width, a length, and a thickness.

12. (Currently Amended) The transistor structure of claim 11 wherein the widths of the ~~source~~ second metal strips are different.

13. (Original) The transistor structure of claim 11 wherein:

the plurality of second metal strips include a second center metal strip and a second outer metal strip, and

the widths of the second metal strips increase from the second center metal strip to the second outer metal strip.

14. (Original) The transistor structure of claim 13 wherein the first center metal strip and the second center metal strip have equal widths.

Claims 15-20 (Cancelled).

21. (New) The transistor structure of claim 1 wherein:

the plurality of first metal strips include a first center metal strip and a first outer metal strip, and

the widths of the first metal strips vary from the first center metal strip to the first outer metal strip.

22. (New) The transistor structure of claim 21 wherein the first metal strips lie orthogonal with respect to the plurality of second conductivity strips.

23. (New) The transistor structure of claim 21 wherein the plurality of second conductivity strips are substantially parallel to each other, and the plurality of first metal strips are substantially parallel to each other.

24. (New) The transistor structure of claim 21 wherein the metal structure further includes a first metal connector, the plurality of first metal strips contacting the first metal connector and extending away from the first metal connector.

25. (New) The transistor structure of claim 21 wherein the metal structure further includes a plurality of spaced-apart second metal strips formed between and spaced apart from the plurality of first metal strips such that a second metal strip lies between each adjacent pair of first metal strips, the plurality of second metal strips being electrically connected to the source strips, the plurality of second metal strips having widths, lengths, and thicknesses such that each second metal strip has a width, a length that is substantially longer than a second metal strip width, and a thickness measured normal to the top surface of the semiconductor material, the widths of the second metal strips being different.

26. (New) The transistor structure of claim 25 wherein:

the plurality of second metal strips include a second center metal strip and a second outer metal strip, and

the widths of the second metal strips vary from the second center metal strip to the second outer metal strip.